



**浩畅半导体**  
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**2SC3125 NPN Transistors**

**SOT-23 Plastic-Encapsulate Transistors**

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客户确认：

公司签章：

部门

工程部

品保部

采购部

签名

日期

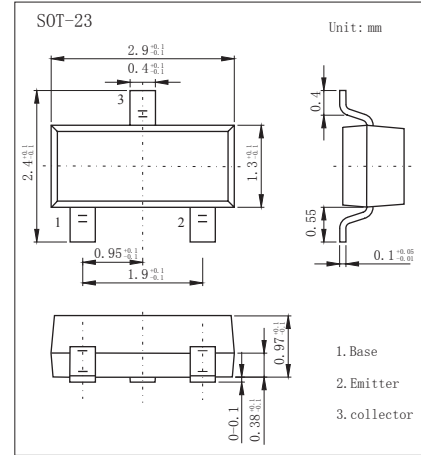


**SOT-23 Plastic-Encapsulate Transistors**

**2SC3125 NPN Transistors**

■ Features

- Collector Current Capability  $I_c=50\text{mA}$
- Collector Emitter Voltage  $V_{CE0}=25\text{V}$



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	30	V
Collector - Emitter Voltage	$V_{CEO}$	25	
Emitter - Base Voltage	$V_{EBO}$	4	
Collector Current - Continuous	$I_c$	50	mA
Base Current	$I_B$	25	
Collector Power Dissipation	$P_c$	150	mW
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 125	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_c= 100 \mu\text{A}, I_E= 0$	30			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_c= 10 \text{mA}, I_B= 0$	25			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E= 100 \mu\text{A}, I_c= 0$	4			
Collector-base cut-off current	$I_{CBO}$	$V_{CB}= 30 \text{V}, I_E= 0$			0.1	uA
Emitter cut-off current	$I_{EBO}$	$V_{EB}= 3\text{V}, I_c=0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=15 \text{mA}, I_B=1.5\text{mA}$			0.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c=15 \text{mA}, I_B=1.5\text{mA}$			1.5	
DC current gain	$h_{FE}$	$V_{CE}= 10\text{V}, I_c= 10\text{mA}$	20		200	
Collector-base time constant	$C_{c rbb'}$	$V_{CB}= 10\text{V}, I_c=1\text{mA}, f=30\text{MHz}$			25	ps
Collector output capacitance	$C_{ob}$	$V_{CB}= 10\text{V}, I_E= 0, f=1\text{MHz}$			1.6	pF
Transition frequency	$f_T$	$V_{CE}= 10\text{V}, I_c= 10\text{mA}$	250			MHz

■ Marking

Marking	HH
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# 2SC3125 NPN Transistors

## Typical Characteristics

